



STIC Search Report

EIC 1700

STIC Database Tracking Number: 124012

TO: George A Goudreau
Location: REM 7A21
Art Unit : 1763
June 8, 2004

Case Serial Number: 09/669159

From: Kendra Mellerson
Location: EIC 1700
REM 4B28
Phone: 571-272-2516

Kendra.Mellerson@uspto.gov

Search Notes

No Cases Reported

US 6,283,131

SEARCH REQUEST FORM

Requestor's Name: George Goudreau Serial Number: 10-650,886
Date: 6-7-041 Phone: 571-272-1434 Art Unit: 1763

Search Topic:

Please write a detailed statement of search topic. Describe specifically as possible the subject matter to be searched. Define any terms that may have a special meaning. Give examples or relevant citations, authors, keywords, etc., if known. For sequences, please attach a copy of the sequence. You may include a copy of the broadest and/or most relevant claim(s).

Litigation Search of US patent 6,046,109
which corresponds to US application 08-998,734,
(for reissue)

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Type of Search
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Vendors
 IG
 STN
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 APS
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 DARC/Questel
 Other

Current session 08/06/2004

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Last connection: 04/06/04 23*15*00

08/06/04 14*19*37

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Query/Command : FILE PLUSPAT

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Search statement 1

Query/Command : US6283131/PN

** SS 1: Results 1

Search statement 2

Query/Command : PRT FULL NONSTOP LEGALALL

1/1 PLUSPAT - ©QUESTEL-ORBIT

PN - US6283131 B1 20010904 [US6283131]
TI - (B1) In-situ strip process for polysilicon etching in deep sub-micron technology
PA - (B1) TAIWAN SEMICONDUCTOR MFG (US)
PA0 - Taiwan Semiconductor Manufacturing Company, Hsin-Chu [TW]
IN - (B1) CHEN HORNG-WEN (TW); WU CHI-HOW (TW)
AP - US66915900 20000925 [2000US-0669159]
PR - US66915900 20000925 [2000US-0669159]
IC - (B1) H01L-021/302
EC - H01L-021/3213D
PCL - ORIGINAL (O) : 134001200; CROSS-REFERENCE (X) : 257E21314
438725000
DT - Basic
CT - US5346586; US5382316; US5767018; US5804088; US5885902; US5976769;
US6037266; US6130166
STG - (B1) U.S. Patent (no pre-grant pub.) after Jan. 2, 2001
AB - A new method of patterning the polysilicon layer in the manufacture of an integrated circuit device has been achieved. A polysilicon layer is provided overlying a semiconductor substrate. The polysilicon layer may overlie a gate oxide layer and thereby comprise the polysilicon gate for MOS devices. A hard mask layer is provided overlying the polysilicon layer. A resist layer is provided overlying the hard mask layer. The resist layer is patterned to form a resist mask that exposes a part of the hard mask layer. The polysilicon layer is patterned in a plasma dry etching chamber. First, the resist layer is optionally trimmed by etching. Second, the hard mask layer is etched where exposed by the resist mask to form a hard mask that exposes a part of the polysilicon layer. Third, the resist mask is stripped away. Fourth, polymer residue from the resist mask is cleaned away using a chemistry containing CF4 gas. Fifth, the polysilicon layer is etched where exposed by the hard mask. After the polysilicon layer is so patterned in the dry plasma etch chamber, the hard mask layer is stripped away to complete the patterning of the polysilicon layer in the manufacture of the integrated circuit device.
UP - 2001-37

1/1 LGST - ©EPO

PN - US6283131 B1 20010904 [US6283131]
AP - US66915900 20000925 [2000US-0669159]
ACT - 20031125 US/RF-A
REISSUE APPLICATION FILED
EFFECTIVE DATE: 20030828
UP - 2003-49

1/1 CRXX - ©CLAIMS/RRX

PN - 6,283,131 A 20010904 [US6283131]
PA - Taiwan Semiconductor Manufacturing Co TW
ACT - 20030828 REISSUE REQUESTED
ISSUE DATE OF O.G.: 20031125
REISSUE REQUEST NUMBER: 10/650886
EXAMINATION GROUP RESPONSIBLE FOR REISSUEPROCESS: 1763

Reissue Patent Number:

Query/Command : FILE INPADOC

PLUSPAT - Time in minutes : 0,41
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Records displayed and billed	:	1	Estimated cost :	0.99 USD
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			Estimated total session cost	2.93 USD

LGST - Time in minutes : 0,02
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Legal-Status informations	:	1	Estimated cost :	0.60 USD
Cost estimated for the last database search	:		Estimated cost :	0.50 USD
Estimated total session cost	:		Cost estimated for the last database search :	1.12 USD
			Estimated total session cost	4.05 USD

CRXX - Time in minutes : 0,03
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Cost estimated for the last database search	:		Estimated cost :	0.50 USD
Estimated total session cost	:		Cost estimated for the last database search :	6.05 USD
			Estimated total session cost	10.10 USD

LITA - Time in minutes : 0,01
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Cost estimated for the last database search	:		Estimated cost :	0.02 USD
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			Estimated total session cost	10.12 USD

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Search statement 1

Query/Command : FAM US6283131/PN

1 Patent Groups

** SS 1: Results 1

Search statement 2

Query/Command : FAMSTATE NONSTOP

1/1 INPADOC - ©INPADOC

PN - US 6283131 BA 20010904 [US6283131]
TI - In-situ strip process for polysilicon etching in deep sub-micron technology
IN - CHEN HORNG-WEN [TW]; WU CHI-HOW [TW]
PA - TAIWAN SEMICONDUCTOR MFG [US]
AP - US 669159/00-A 20000925 [2000US-0669159]
PR - US 669159/00-A 20000925 [2000US-0669159]
IC - H01L-021/302

1/1 LEGALI - ©EPO

PN - US6283131 B1 20010904 [US6283131]
AP - US66915900 20000925 [2000US-0669159]
ACTE - 20031125 US/RF-A
REISSUE APPLICATION FILED
EFFECTIVE DATE: 20030828
UP - 2003-49

PATNO IS 6283131

DATE: JUNE 8, 2004
LIBRARY: PATENT
FILE: ALL

Your search request is:

PATNO IS 6283131

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LEVEL 1... 1

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To MODIFY your search request, press the M key (for MODIFY) and then the ENTER key.

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LEVEL 1 - 1 PATENT

1. 6283131 , September 4, 2001 , In-situ strip process for polysilicon etching in deep sub-micron technology, Chen, Horng-Wen - Taichung, Taiwan (TW); Wu, Chi-How - Tainan, Taiwan (TW), 669159 (09), Taiwan Semiconductor Manufacturing Company, Hsin-Chu, Taiwan (TW), 03, September 25, 2000 - ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS)., TAIWAN SEMICONDUCTOR MANUFACTURING COMPANY SCIENCE-BASED INDUSTRIAL PARK 121 PARK AVE. 3 HSIN- CHU R.O.C. TAIWAN, Reel and Frame Number: 011182/0578

CORE TERMS: layer, polysilicon, mask, etch, resist, chamber, photoresist, plasma, sccm, dry ...

LEVEL 1 - 1 OF 1 PATENT

UNITED STATES PATENT AND TRADEMARK OFFICE GRANTED PATENT

6283131

<=1> Get Drawing Sheet 1 of 7

September 4, 2001

In-situ strip process for polysilicon etching in deep
sub-micron technology

REISSUE: August 28, 2003 - Reissue Application filed Ex. Gp.: 1763; Re. S.N.
10/650,886 (O.G. November 25, 2003)

APPL-NO: 669159 (09)

FILED-DATE: September 25, 2000

GRANTED-DATE: September 4, 2001

CORE TERMS: layer, polysilicon, mask, etch, resist, chamber, photoresist,
plasma, sccm, dry ...

6283131 OR 6,283,131

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